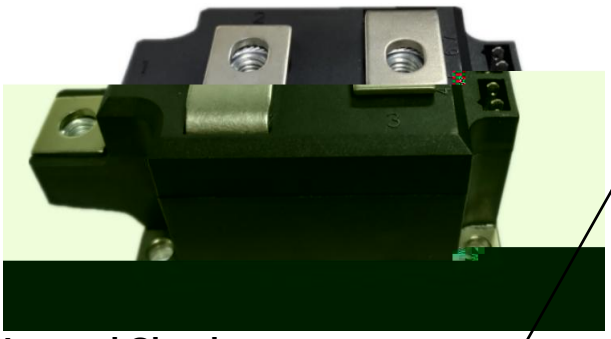
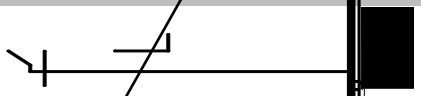


Features

- International standard package
- High Surge Capability
- Simple Mounting

Internal Circuit



Blocking - Off State

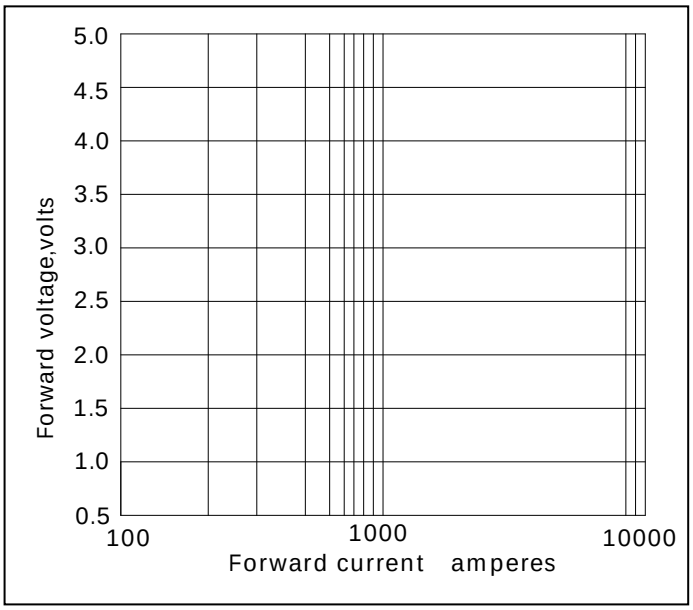
TYPE		V_{DRM}/V_{RRM}	V_{DSM}/V_{RSM}	Units
MT200C(A/K)28T3	MT200C(A/K)B28T3	2800	2900	V
MT200C(A/K)30T3	MT200C(A/K)B30T3	3000	3100	V
MT200C(A/K)32T3	MT200C(A/K)B32T3	3200	3300	V
MT200C(A/K)34T3	MT200C(A/K)B34T3	3400	3500	V
MT200C(A/K)36T3	MT200C(A/K)B36T3	3600	3700	V

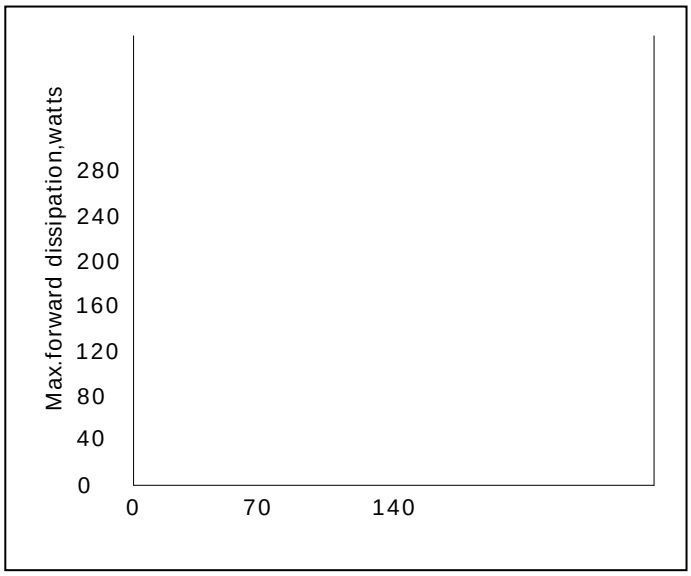
Maximum Ratings

Symbol	Conditions	Values	Units
I_{TAV}	Sine 180°;Tc=85	200	A
I_{TSM}	T_{VJ}=125 t=10ms, sine	6000	A
I^2t	T_{VJ}=125 t=10ms, sine	180000	A
Visol	a.c.50HZ;r.m.s.;1min,I_{iso}:2mA(MAX)	4000	
Tvj		-40 to 125	
Tstg		-40 to 125	
Mt	To terminals(M8)	12±15%	
Ms	To heatsink(M6)	6±15%	
di/dt	T_{VJ}= T_{VJM} ,V_{DM}≤2/3V_{DRM} I_{GM}=1.5A,≤0.5μs	100	
dv/dt	T_{VJ}= T_{VJM} ,2/3V_{DRM}, linear voltage rise	10	
Weight	Module(Approximately)		

Thermal Characteristics

Symbol	Conditions	
Rth(j-c)	per chip	
Rth(c-h)	per chip	


5.0
4.5
4.0
3.5
3.0
2.5
2.0
1.5
1.0
0.5
Forward voltage,volts
100
1000
10000
Forward current amperes


Max.forward dissipation,watts
280
240
200
160
120
80
40
0
0
70
140